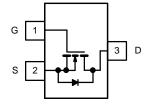


N-Channel 100 V (D-S) MOSFET

MOSFET PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)		
	0.120 at V_{GS} = 10 V	2.3			
100	0.140 at V _{GS} = 6 V	2.1	2.9 nC		
	0.150 at V _{GS} = 4.5 V	1.7			



FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
 100 % UIS Tested
- Material categorization:



APPLICATIONS

- DC/DC Converters
- · Load Switch
- LED Backlighting in LCD TVs

Parameter		Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage	V _{GS}	± 20	v	
	T _C = 25 °C		2.3	
Continuous Drain Current ($T_1 = 150 \text{ °C}$)	T _C = 70 °C	1_	1.8	
	T _A = 25 °C	I _D	1.6 ^{b, c}	
	T _A = 70 °C		1.3 ^{b, c}	Α
Pulsed Drain Current (t = 300 µs)		I _{DM}	7.5	A
Continuous Source-Drain Diode Current	T _C = 25 °C	1.	2.1	
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	1.0 ^{b, c}	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	5	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	1.25	mJ
	T _C = 25 °C		2.5	
Maximum Power Dissipation	T _C = 70 °C	PD	1.6	w
	T _A = 25 °C	'D	1.25 ^{b, c}	VV
	T _A = 70 °C		0.8 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stq}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^{b, d}	≤ 5 s	R _{thJA}	75	100	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	50			
Nataa							

Notes:

a. Based on T_C = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. Maximum under steady state conditions is 166 °C/W.

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MOSFET SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				Г	1	1	
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 V, I_{D} = 250 \mu A$	100			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		105		mV/°	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			5.2			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.2		2.8	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$			1	Δ	
Zelo Gale Volage Dialit Guitent	USS	V_{DS} = 100 V, V_{GS} = 0 V, T_{J} = 55 °C			10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \geq 5$ V, V_{GS} = 4.5 V	5			А	
		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 1.5 \text{ A}$		0.115	0.120		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 6 V, I _D = 1 A		0.132	0.140	Ω	
		$V_{GS} = 4.5 \text{ V}, I_{D} = 0.5 \text{ A}$		0.141	0.150	1	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 20 V, I _D = 1.5 A		2.0		S	
Dynamic ^b				1		1	
Input Capacitance	C _{iss}			190			
Output Capacitance	C _{oss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		22		pF	
Reverse Transfer Capacitance	C _{rss}			13			
		V _{DS} = 50 V, V _{GS} = 10 V, I _D = 1.6 A		5.2	10.4	+	
Total Gate Charge	Qg			2.9	5.8	- nC	
Gate-Source Charge	Q _{gs}	V _{DS} = 50 V, V _{GS} = 4.5 V, I _D = 1.6 A		0.75	0.0		
Gate-Drain Charge	Q _{gd}	v DS = 00 v, v GS = 1.0 v, 1D = 1.0 v		1.4			
Gate Resistance	∽gu R _g	f = 1 MHz	0.3	1.4	2.8	Ω	
Turn-On Delay Time	-		0.5	30	45	52	
Rise Time	t _{d(on)}	V = 50 V B = 20 O		26	43 39	-	
	t _r	$V_{\text{DD}} = 50 \text{ V}, \text{ R}_{\text{L}} = 39 \Omega$ $\text{I}_{\text{D}} = 1.3 \text{ A}, \text{ V}_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		17			
Turn-Off Delay Time	t _{d(off)}	$1D = 1.0$ / $3, V_{GEN} = 4.0$ $3, V_{g} = 1.22$			26		
Fall Time	t _f			12	20	ns	
Turn-On Delay Time	t _{d(on)}			6	12	-	
Rise Time	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 39 \Omega$		10	20		
Turn-Off Delay Time	t _{d(off)}	I_D = 1.3 A, V_{GEN} = 10 V, R_g = 1 Ω		10	20		
Fall Time	t _f			6	12		
Drain-Source Body Diode Characterist	1.	7 07 00		Г	1	1	
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C			2.1	A	
Pulse Diode Forward Current ^a	I _{SM}				7.5		
Body Diode Voltage	V _{SD}	I _S = 1.3 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			22	33	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 1.3 A, dl/dt = 100 A/μs, T _{.1} = 25 °C		21	32	nC	
Reverse Recovery Fall Time	t _a	F = 1.5 A, and = 100 A/		16			
Reverse Recovery Rise Time	t _b			6	1	ns	

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

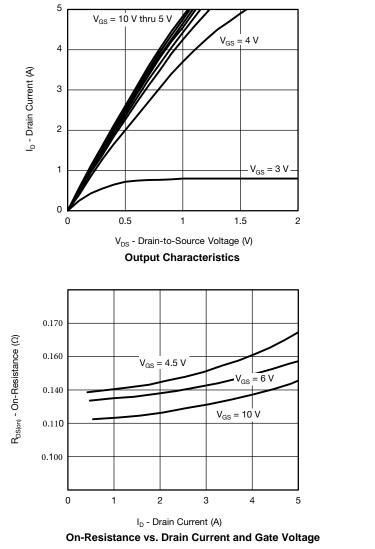
b. Guaranteed by design, not subject to production testing.

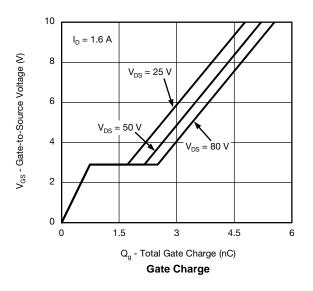
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

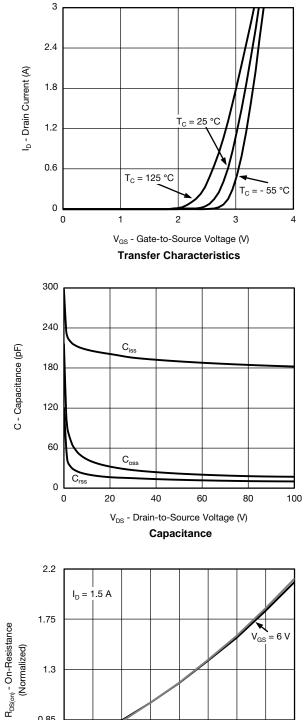


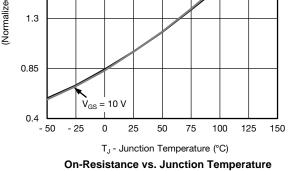
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





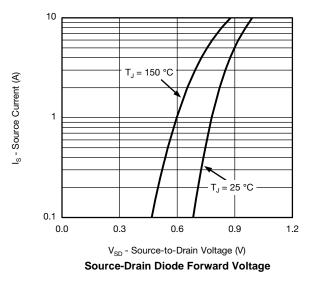


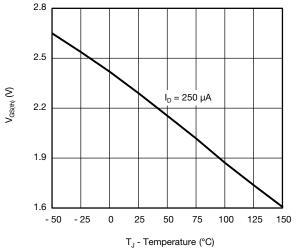


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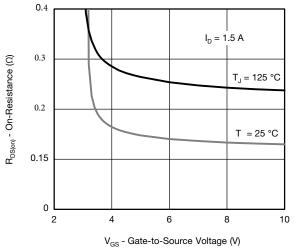
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

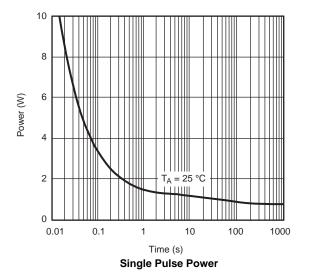


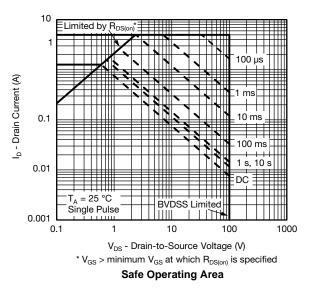






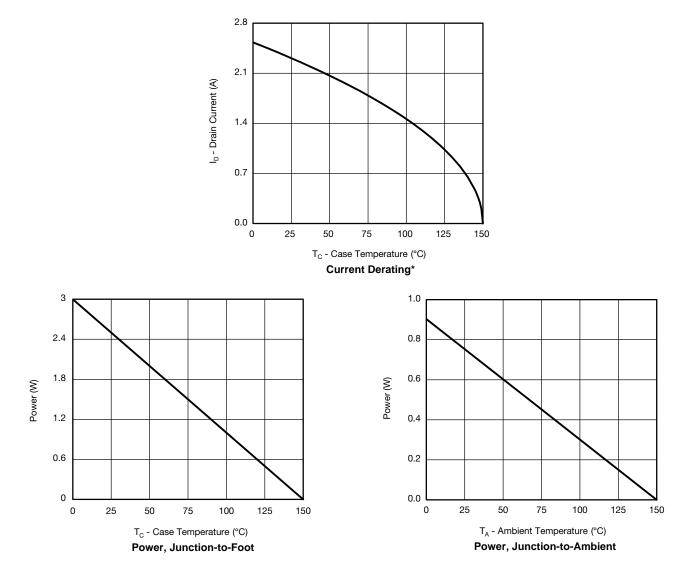
On-Resistance vs. Gate-to-Source Voltage







TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

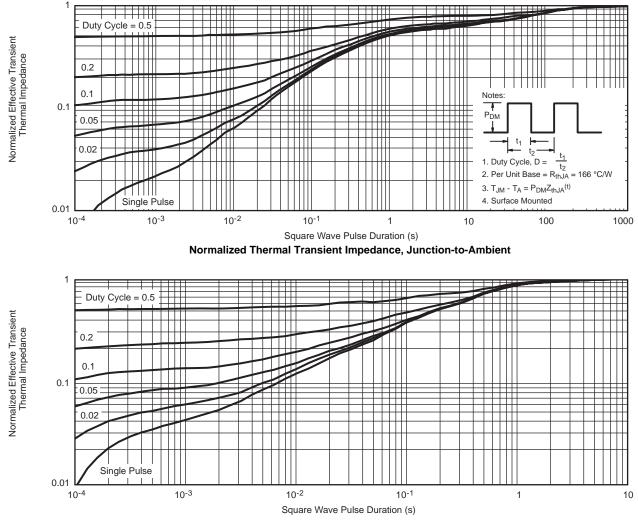


* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

The characteristics shown in the two graphs

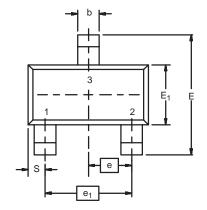
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

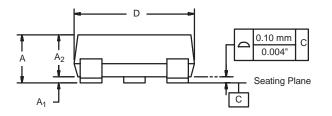
- Normalized Transient Thermal Impedance Junction-to-Foot (25 C)

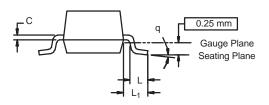
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SOT-23 (TO-236): 3-LEAD



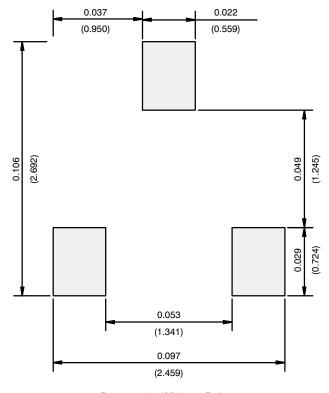




Dim –	MILLIM	ETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95	BSC	0.0374 Ref		
e ₁	1.90	BSC	0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025	Ref	
S	0.50 Ref		0.020	Ref	
q	3°	8°	3°	8°	



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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